

Title (en)

METHOD FOR PRODUCING INTEGRATED CIRCUITS PROVIDED WITH SILICON- GERMANIUM HETERO-BIPOLAR TRANSISTORS

Title (de)

VERFAHREN ZUR HERSTELLUNG INTEGRIERTER SCHALTKREISE MIT SILIZIUM- GERMANIUM-HETEROBIPOLARTRANSISTOREN

Title (fr)

PROCEDE DE PRODUCTION DE CIRCUITS INTEGRES AYANT DES TRANSISTORS HETEROBIPOLAIRES SILICIUM-GERMANIUM

Publication

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Application

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Abstract (en)

[origin: WO2006081987A1] The invention relates to a method of producing integrated circuits provided with silicon-germanium hetero-bipolar transistors. A collector semiconductor area is produced, wherein an etching stop layer is produced on a connecting region and an opening is introduced into said etching stop layer. Semi-conductor material is applied over the etching stop layer and over the opening and is monocrystalline at least in the collector semiconductor area above the opening. A masking layer is applied to the semiconductor material prior to etching the semiconductor material above the collector semiconductor area, said masking layer protecting the collector semiconductor area prior to etching. Subsequently, the semiconductor material is etched until the etching stop layer is reached. Said etching stop layer stops etching when a defining surface between the semiconductor material and the etching stop layer is detected during etching and etching is stopped according to said detection.

IPC 8 full level

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CPC (source: EP US)

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